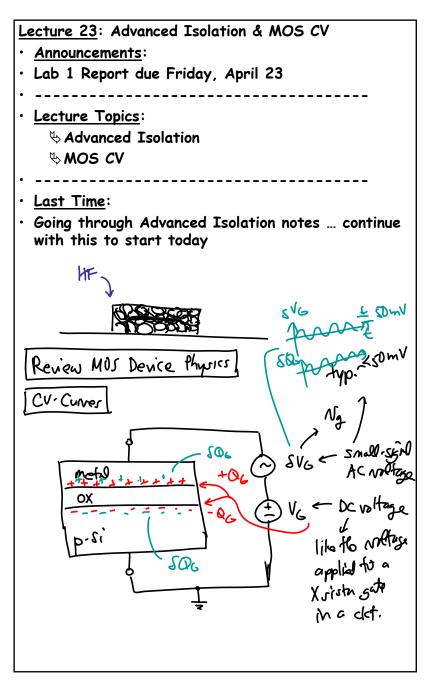
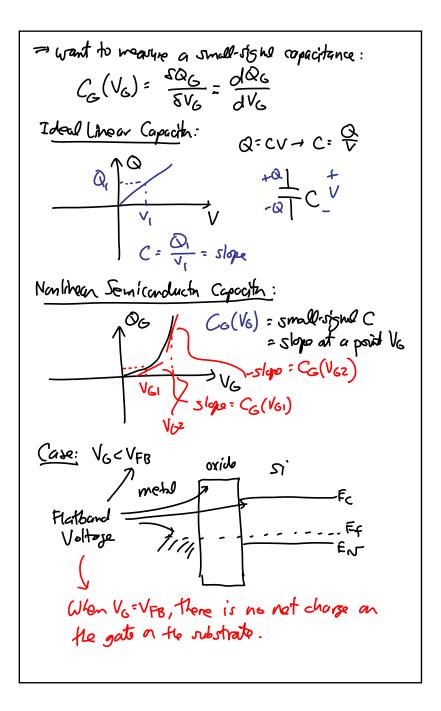
<u>EE 143</u>: Microfabrication Technology <u>Lecture 23c</u>: Advanced Isolation & MOS CV





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> Cox Evy SVG Μ + V6 < VFB 0 p-si accumulation Xex= galo oxide thidered Cax: gate oxide capacitance [Cpenunit area] CVCurve Cox JN CG $\overline{V}_{\mathcal{C}}$ VFB VG < VFB (accumulation) Case: K. VFB - no chape

Case: VG=VFB (but VG<V4) (Threshold voltage Charge begins to tam in the semiconductor SNG. $\widehat{}$ m+ 0X Rox] 0000000 1 V6 > VFB p-5i ~~ (VG) gets lapper as VG1 ··· Co(VG) I fixed nog. charge V dopletin regim $\frac{\prod_{i=1}^{n} C_{eq} \cdot \frac{\epsilon_{eq}}{\chi_{eq}}}{\prod_{i=1}^{n} C_{b}(V_{6}) \cdot \frac{\epsilon_{si}}{\chi_{d}(V_{6})}}$

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